## **IN THE CLAIMS:**

1. (Currently Amended) A chuck assembly of an etching apparatus, the chuck assembly comprising:

a chuck body comprising a stepped portion at an edge side portion of the chuck body, for supporting a central portion of a wafer to be etched;

an edge ring, received in the stepped portion of the chuck body, for supporting an edge portion of the wafer to be etched, wherein the edge ring has less resistivity than the resistivity of a silicon wafer and wherein the edge ring comprises a slanted step portion whose surface forms an angle in a range of about more than 55 to about 80 degrees relative to a normal to the wafer surface, wherein the slanted step portion of the edge ring begins from about 1.5 to about 4.5 mm from the edge portion of the wafer to be etched; and

an insulating ring provided at a surrounding portion of the chuck body, for supporting a bottom portion of the edge ring, the bottom portion of the edge ring being extended toward outside of the chuck body.

- 2. (Canceled)
- 3. (Canceled)
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)

7. (Previously Presented) A chuck assembly for a semiconductor etching apparatus, the chuck assembly comprises:

a chuck body for supporting a semiconductor wafer to be etched;

an edge ring, disposed on the chuck body, for supporting an edge portion of the wafer to be etched, wherein the edge ring comprises a slanted step portion whose surface forms an angle in a range of more than 55 degrees to about 80 degrees relative to a normal to the wafer surface, wherein the slanted step portion of the edge ring begins from about 1.5 to about 2.5 mm from the edge portion of the wafer to be etched; and

an insulating ring, disposed on the outside portion of the chuck body, for supporting the edge ring;

— wherein the electrical resistivity of the edge ring is less than the electrical resistivity of a silicon wafer.

- 8. (Canceled)
- 9. (Canceled)
- 10. (Canceled)
- 11. (Canceled)
- 12. (Canceled)